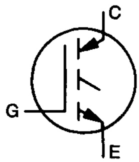
International IOR Rectifier

PD-9.719A

IRGMC50U

INSULATED GATE BIPOLAR TRANSISTOR

UltraFast™ IGBT



n-channel

Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of higher-voltage, higher-current applications.

The performance of various IGBTs varies greatly with frequency. Note that IR now provides the designer with a speed benchmark ($f_{Ic/2}$, or the "half-current frequency"), as well as an indication of the current handling capability of the device. Refer to Figure 14.

Product Summary

Part Number	V_{CE}	$V_{CE(on)}$	I_C	E_{ts}
IRGMC50U	600V	3.0V	35A*	2.8 mJ

Features:

- Electronically Isolated and Hermetically Sealed
- Simple Drive Requirements
- Latch-proof
- Ultra-fast operation > 10 kHz
- Switching-Loss Rating includes all "tail" losses
- Ceramic eyelets

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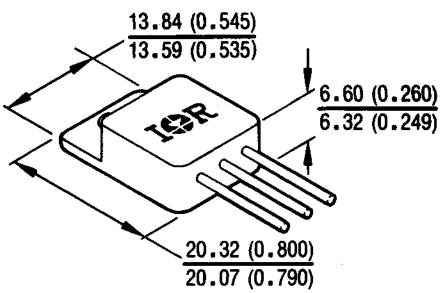
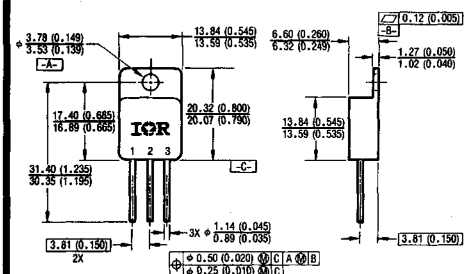
CASE STYLE AND DIMENSIONS



CAUTION

BERYLLIA WARNING PER MIL-S-19500
SEE PAGE G-105



NOTES:
1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M - 1982.
2 ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).

LEGEND
1 COLLECTOR
2 EMITTER
3 GATE

**For leadform configuration see page G-105, fig. 15

Conforms to JEDEC Outline TO-254AA**
Dimensions in Millimeters and (Inches)

*I_C current limited by pin diameter

Absolute Maximum Ratings

	Parameter	Max.	Units
I_C @ T_C = 25°C	Continuous Collector Current	35*	A
I_C @ T_C = 100°C	Continuous Collector Current	20	
I_{CM}	Pulsed Collector Current ①	160	
V_{CE}	Collector-to-Emitter Breakdown Voltage	600	V
V_{GE}	Gate-to-Emitter Voltage	±20	
I_{LM}	Clamped Inductive Load Current ②	160	A
P_D @ T_C = 25°C	Maximum Power Dissipation	150	W
P_D @ T_C = 100°C	Maximum Power Dissipation	60	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Lead Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Weight	9.3 (typical)	g

*I_C current limited by pin diameter

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.83	K/W ⑤
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.12	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	48	

Electrical Characteristic @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V_{GE} = 0V, I_C = 1.0 mA
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Volt. ③	23	—	—		V_{GE} = 0V, I_C = 1.0A
$\Delta V_{(BR)CES}/\Delta T_J$	Temp. Coeff. of Breakdown Voltage	—	0.60	—	V/°C	V_{GE} = 0V, I_C = 1.0 mA
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	—	3.0	V	V_{GE} = 15V, I_C = 20A See Fig. 4
		—	2.4	—		V_{GE} = 15V, I_C = 35A
		—	1.9	—		V_{CE} = 15V, I_C = 20A, T_J = 125°C
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		V_{CE} = V_{GE}, I_C = 250 μA
$\Delta V_{GE(th)}/\Delta T_J$	Temp. Coeff. of Threshold Voltage	—	-13	—	mV/°C	V_{CE} = V_{GE}, I_C = 250 μA
g_{fe}	Forward Transconductance ④	16	—	—	S	V_{CE} ≥ 15V, I_C = 20A
I_{CES}	Zero Gate Voltage Collector Current	—	—	50	μA	V_{GE} = 0V, V_{CE} = 480V, T_J = 25°C
		—	—	5000		V_{GE} = 0V, V_{CE} = 480V, T_J = 125°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±500	nA	V_{GE} = ±20V

Notes:

① Repetitive rating; V_{GE} = 20V, pulse width limited by max. junction temperature (See figure 12b).

② V_{CC} = 80% (BV_{CES}), V_{GE} = 20V, L ≥ 10 μH, R_G = 10Ω, (See figure 12a)

③ Pulse width ≤ 80 μs; duty factor ≤ 0.1%.

④ Pulse width ≤ 5 μs, single shot

⑤ K/W equivalent to °C/W

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Q_G	Total Gate Charge (turn-on)	—	115	140	nC	I_C = 20A, V_{CC} = 300V
Q_{GE}	Gate - Emitter Charge (turn-on)	—	15	35		See Figure 6.
Q_{GC}	Gate - Collector Charge (turn-on)	—	35	70		V_{GE} = 15V
$t_{d(on)}$	Turn-On Delay Time	—	—	50	ns	See test circuit, figure 13.
t_r	Rise Time	—	—	75		I_C = 20A, V_{CC} = 480V
$t_{d(off)}$	Turn-Off Delay Time	—	—	300		T_J = 25°C
t_f	Fall Time	—	—	210		V_{GE} = 15V, R_G = 2.35Ω
E_{on}	Turn-On Switching Loss	—	0.12	—	mJ	Energy losses include "tail".
E_{off}	Turn-Off Switching Loss	—	1.6	—		Also see figures 9, 10, & 11.
E_{ts}	Total Switching Loss	—	1.7	2.8		
$t_{d(on)}$	Turn-On Delay Time	—	24	—	ns	I_C = 20A, V_{CC} = 480V
t_r	Rise Time	—	27	—		T_J = 125°C
$t_{d(off)}$	Turn-Off Delay Time	—	180	—		V_{GE} = 15V
t_f	Fall Time	—	130	—		R_G = 2.35Ω
E_{ts}	Total Switching Loss	—	2.7	—	mJ	
L_E	Internal Emitter Inductance	—	8.7	—	nH	Measured 5mm from package.
C_{ies}	Input Capacitance	—	2900	—	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	—	330	—		V_{CC} = 30V See fig 5.
C_{res}	Reverse Transfer Capacitance	—	41	—		f = 1.0 MHz
C_{CC}	Collector-to-Case Capacitance	—	12	—		

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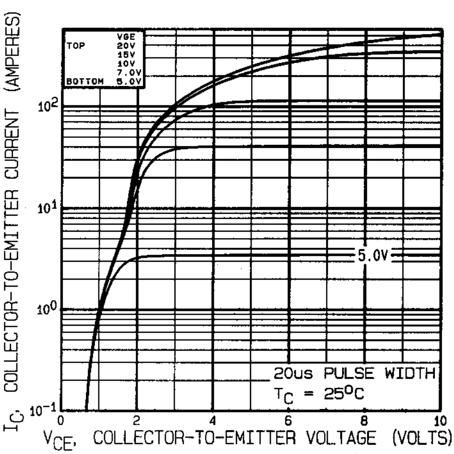

Fig. 1 — Typical Output Characteristics, T_C = 25°C

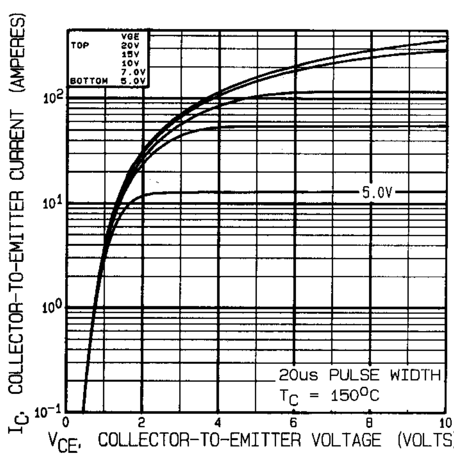

Fig. 2 — Typical Output Characteristics, T_C = 150°C

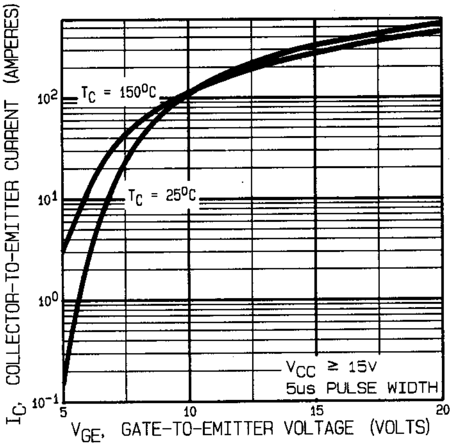

Fig. 3 — Typical Transfer Characteristics

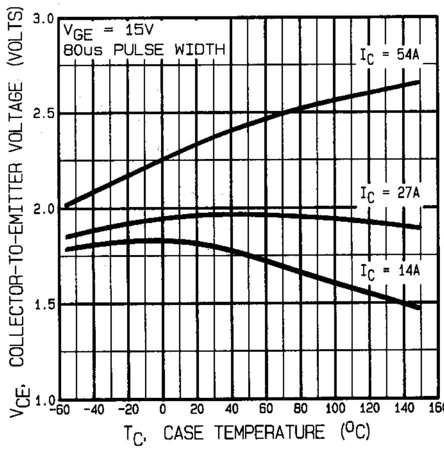

Fig. 4 — Collector-to-Emitter Saturation Voltage vs. Case Temperature

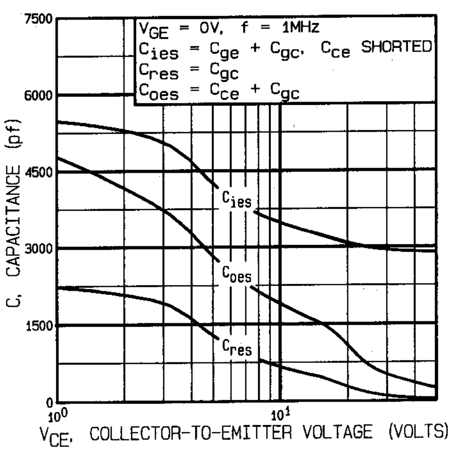

Fig. 5 — Typical Capacitance vs. Collector-to-Emitter Voltage

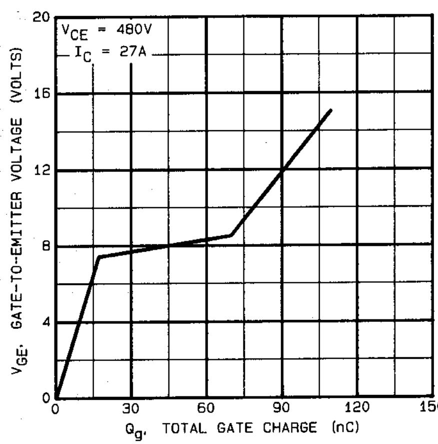

Fig. 6 — Typical Gate Charge vs. Gate-to-Emitter Voltage

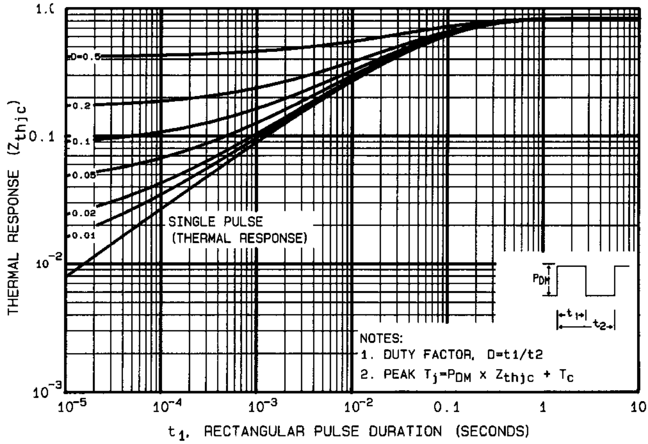

Fig. 7 — Maximum Effective Transient Thermal Impedance, Junction-to-Case

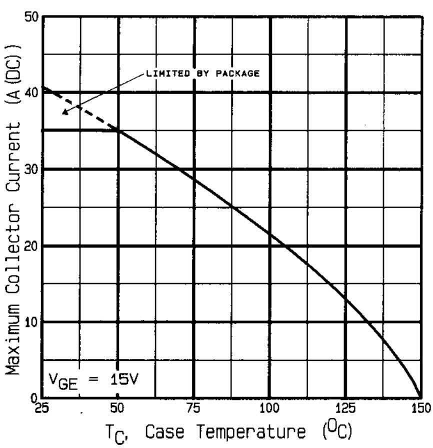

Fig. 8 — Maximum Collector Current vs. Case Temperature

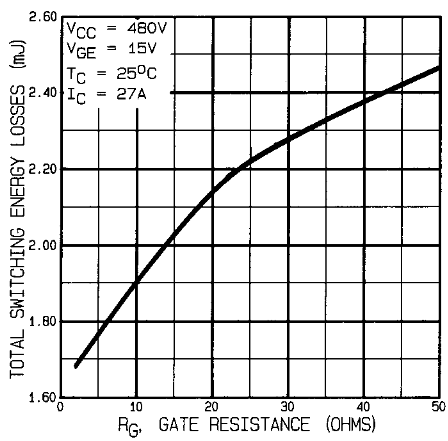

Fig. 9 — Typical Switching Losses vs. Gate Resistance

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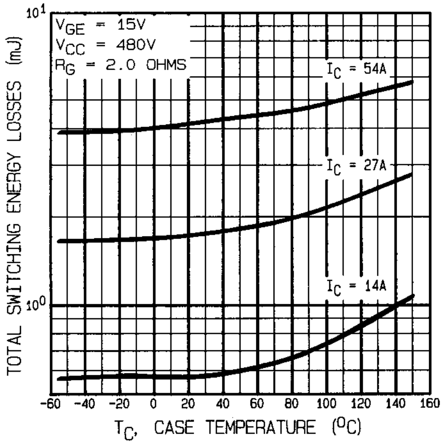


Fig. 10 — Typical Switching Losses vs. Case Temperature

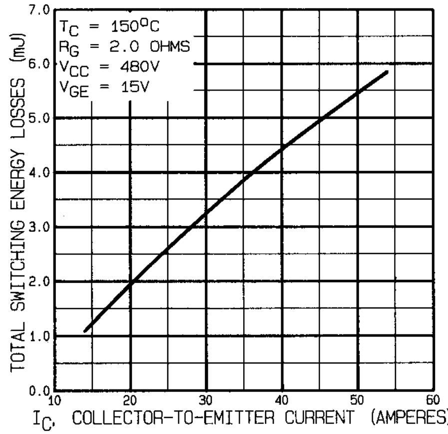


Fig. 11 — Typical Switching Losses vs. Collector-to-Emitter Current

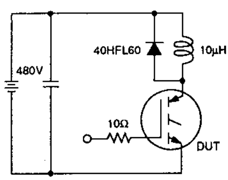


Fig 12a. Clamped Inductive Load Test Circuit

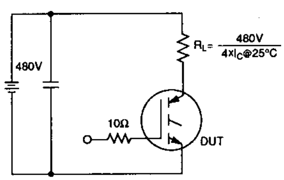


Fig 12b. Pulsed Collector Current Test Circuit

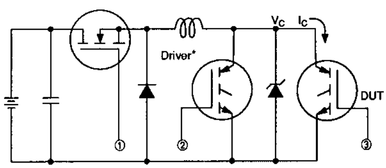


Fig 13a. Switching Loss Test Circuit

* Driver same type as DUT, V_C = 480V

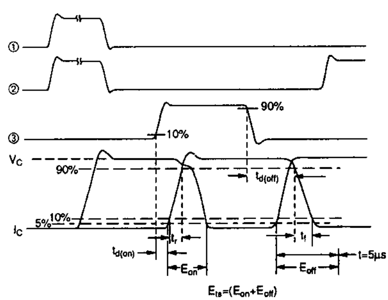


Fig 13b. Switching Loss Waveforms

For both, power dissipation = 34W

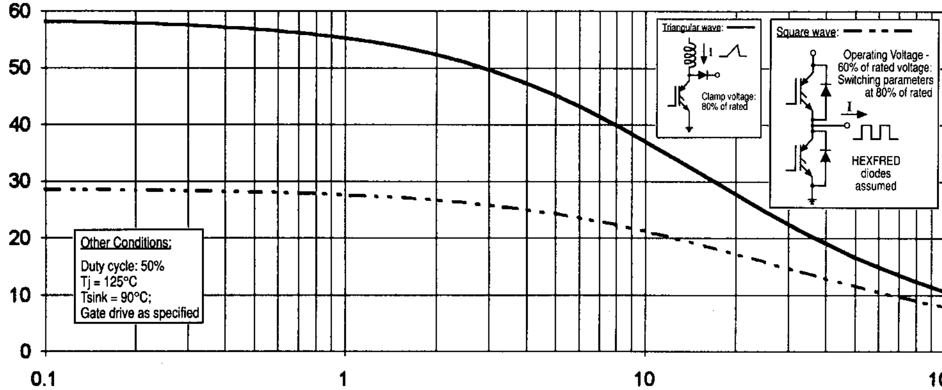
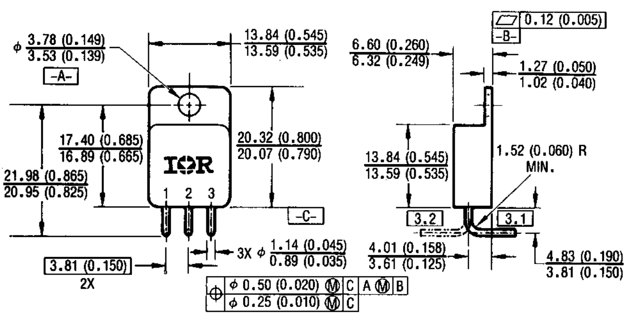


Fig. 14 — Typical Load Current vs. Frequency
(For square wave, $I = I_{RMS}$ of fundamental; for triangular wave, $I = I_{PK}$)



NOTES:
1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M - 1982.
2 ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3 LEADFORM IS AVAILABLE IN EITHER ORIENTATION:
3.1 EXAMPLE: IRGMC50UD
3.2 EXAMPLE: IRGMC50UU

LEGEND
1 COLLECTOR
2 EMITTER
3 GATE

Fig. 15 – Optional Leadforms for Outline TO-254

BERYLLIA WARNING PER MIL-S-19500
Packages containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.